Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.8)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D = V_{DRM} T_j =150 R_L =3.3k	- -			

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

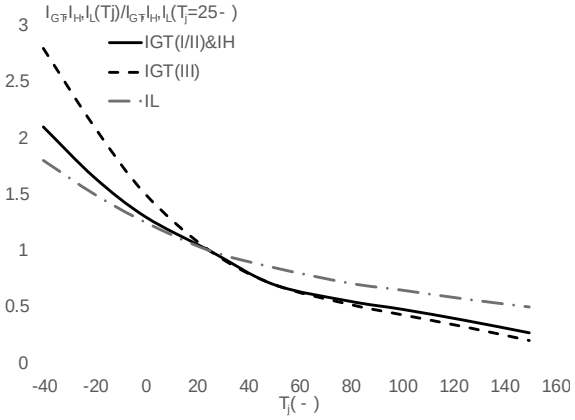
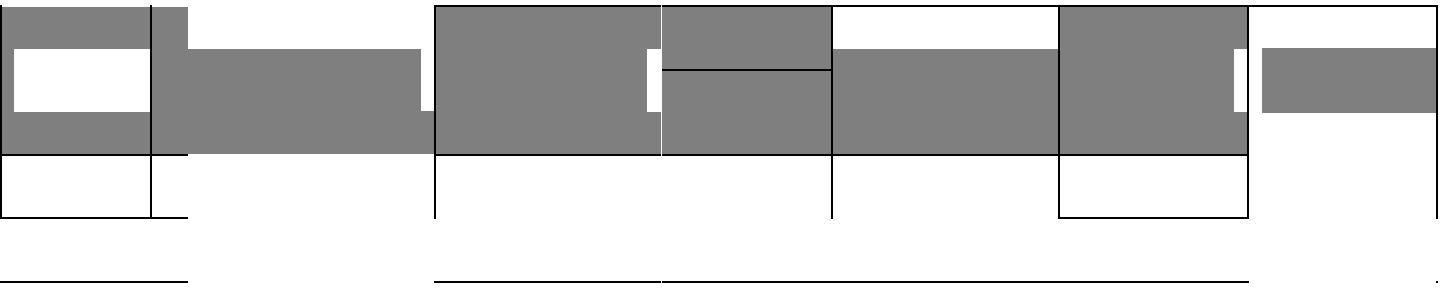
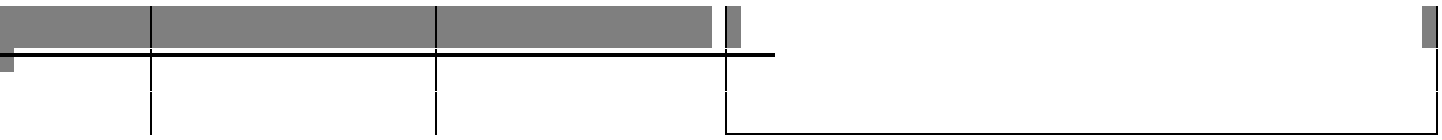


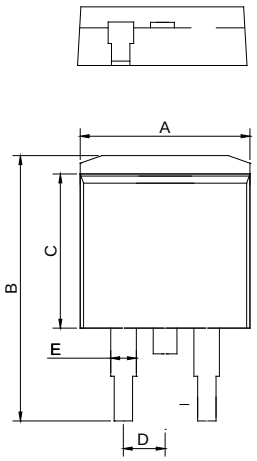
FIG.8 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards







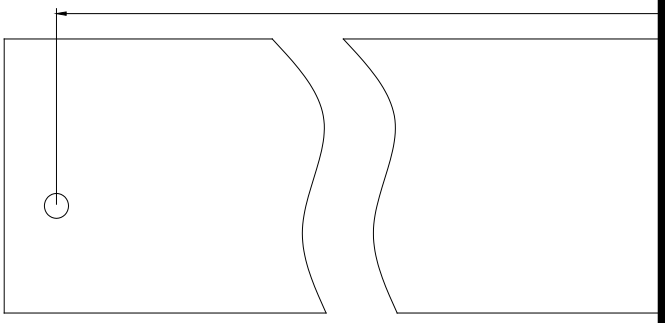
PACKAGE MECHANICAL DATA E



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.40		9.60	0.370		0.378
D	2.40			0.094		
E	1.20		1.50	0.047		0.059
F	0.75		0.85	0.029		0.033

T1610H-6E

DELIVERY MODE



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